

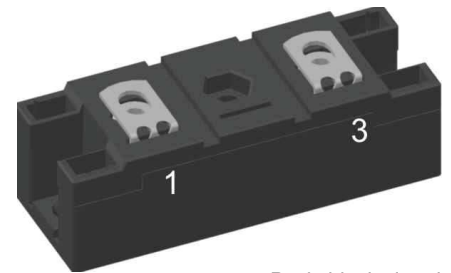
Fast Recovery Epitaxial Diode (FRED)

$$\begin{aligned} V_{RRM} &= 200 \text{ V} \\ I_{FAVM} &= 582 \text{ A} \\ t_{rr} &= 150 \text{ ns} \end{aligned}$$

Single Diode

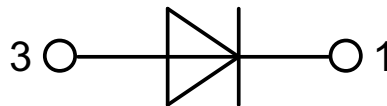
Part number

MEO 550-02DA



Backside: isolated

 E72873



Features / Advantages:

- International standard package with DCB ceramic base plate
- Planar passivated chips
- Short recovery time
- Low switching losses
- Soft recovery behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Applications:

- Antiparallel diode for high frequency switching devices
- Free wheeling diode in converters and motor control circuits
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Package: Y4-M6

- Isolation voltage: 3600 V~
- Industry standard outline
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

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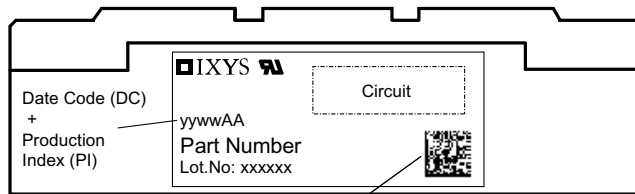


Diode				Ratings			
Symbol	Definitions	Conditions		min.	typ.	max.	
V_{RSM}	max. non-repetitive reverse		$T_{VJ} = 25^{\circ}\text{C}$			200	V
V_{RRM}	max. repetitive reverse		$T_{VJ} = 25^{\circ}\text{C}$			200	V
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$			5	mA
		$V_R = 0.8 \cdot V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$			4	mA
		$V_R = 0.8 \cdot V_{RRM}$	$T_{VJ} = 125^{\circ}\text{C}$			160	mA
V_F	forward voltage	$I_F = 300 \text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.10	V
			$T_{VJ} = 125^{\circ}\text{C}$			0.84	V
		$I_F = 520 \text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.25	V
			$T_{VJ} = 125^{\circ}\text{C}$			1.08	V
I_{FRMS}	RMS forward current		$T_C = 75^{\circ}\text{C}$			822	A
I_{FAVM} ①	max. average forward current	rectangular, d = 0.5	$T_C = 75^{\circ}\text{C}$			582	A
V_{TO}	threshold voltage	for power-loss calculations only	$T_{VJ} = T_{VJM}$			0.52	V
r_T	slope resistance					1.06	mΩ
R_{thJC}	thermal resistance junction to case				0.043	0.071	K/W
R_{thCH}	thermal resistance junction to heatsink						K/W
P_{tot}	total power dissipation		$T_{VJ} = 25^{\circ}\text{C}$			1750	W
I_{FSM}	max. surge forward current	t = 10 ms (50 Hz), sine	$T_{VJ} = 45^{\circ}\text{C}$			4.80	kA
		t = 8.3 ms (60 Hz), sine				5.28	kA
		t = 10 ms (50 Hz), sine	$T_{VJ} = 150^{\circ}\text{C}$			4.32	kA
		t = 8.3 ms (60 Hz), sine				4.75	kA
I^2t	I^2t value for fusing	t = 10 ms (50 Hz), sine	$T_{VJ} = 45^{\circ}\text{C}$			115.2	kA ² s
		t = 8.3 ms (60 Hz), sine				117.1	kA ² s
		t = 10 ms (50 Hz), sine	$T_{VJ} = 150^{\circ}\text{C}$			93.3	kA ² s
		t = 8.3 ms (60 Hz), sine				94.8	kA ² s
t_{rr}	max. reverse recovery current	$I_F = 500 \text{ A}; -di_F/dt = 200 \text{ A}/\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$		60	100	ns
			$T_{VJ} = 100^{\circ}\text{C}$		150	200	ns
I_{RM}	reverse recovery time	$V_R = 100 \text{ V}; L \leq 0.05 \mu\text{H}$	$T_{VJ} = 25^{\circ}\text{C}$		7	9	A
			$T_{VJ} = 100^{\circ}\text{C}$		13	15	A

① I_{FAVM} rating includes reverse blocking losses at T_{VJM} , $V_R = 0.8 V_{RRM}$, duty cycle d = 0.5

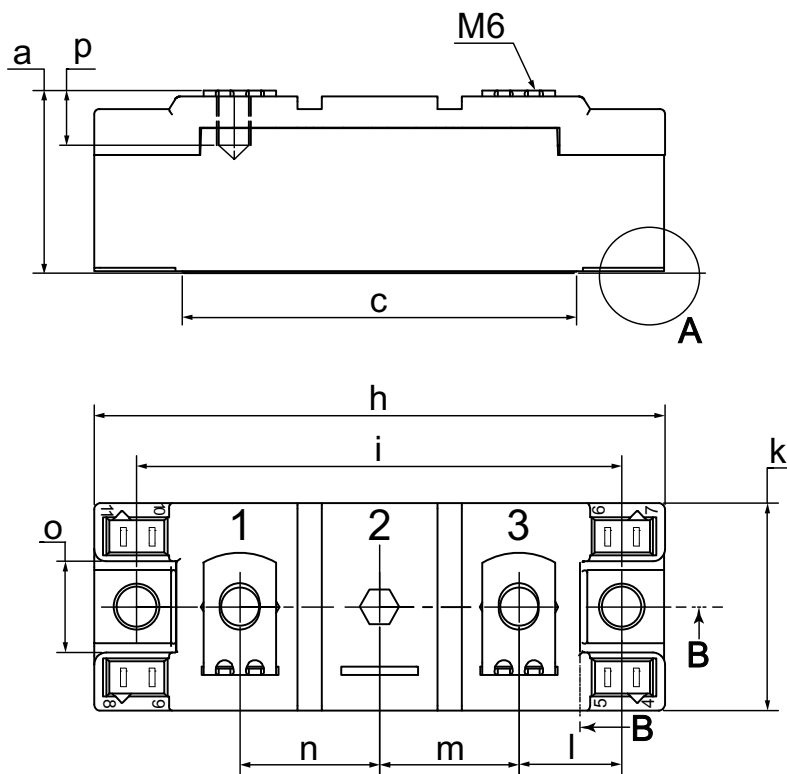


Package Y4-M6				Ratings			
Symbol	Definitions	Conditions		min.	typ.	max.	
I_{RMS}	RMS current	per terminal				300	A
T_{VJ}	virtual junction temperature			-40		150	°C
T_{op}	operation temperature			-40		125	°C
T_{stg}	storage temperature			-40		125	°C
Weight					108		g
M_D	mounting torque			2.25		2.75	Nm
M_T	terminal torque			4.5		5.5	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	14.0	10.0			mm
$d_{Spb/Apb}$			16.0	16.0			mm
V_{ISOL}	isolation voltage	$t = 1$ second $t = 1$ minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3600 3000			V V

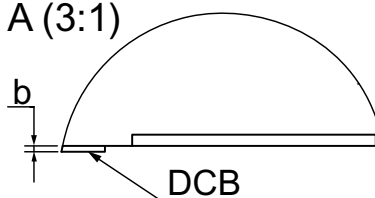
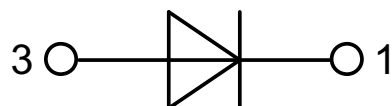
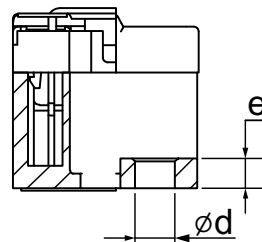


Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MEO 550-02DA	MEO 550-02DA	Box	6	464651

Outlines Y4-M6


Dim.	MIN [mm]	MAX [mm]	MIN [inch]	MAX [inch]
a	30.0	30.6	1.181	1.205
b	typ. 0.25		typ. 0.010	
c	64.0	65.0	2.520	2.559
d	6.5	7.0	0.256	0.275
e	4.9	5.1	0.193	0.201
h	93.5	94.5	3.681	3.720
i	79.5	80.5	3.130	3.169
k	33.4	34.0	1.315	1.339
l	16.7	17.3	0.657	0.681
m	22.7	23.3	0.894	0.917
n	22.7	23.3	0.894	0.917
o	14.0	15.0	0.551	0.591
p	typ. 10.5		typ. 0.413	

A (3:1)

B-B (1:1)


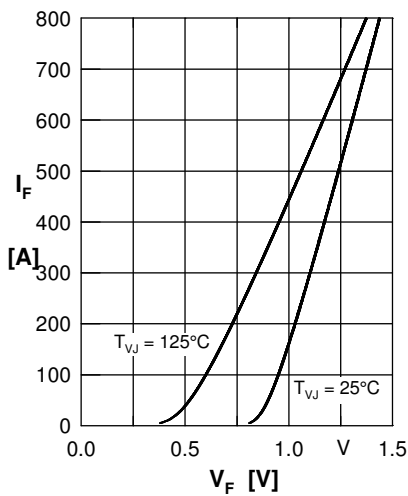
Curves


Fig. 1 Forward current I_F vs voltage drop V_F per leg

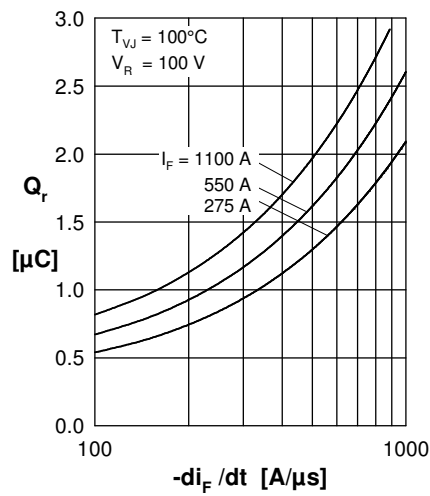


Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$

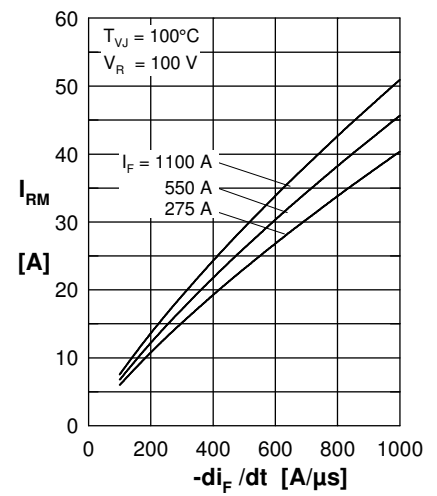


Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

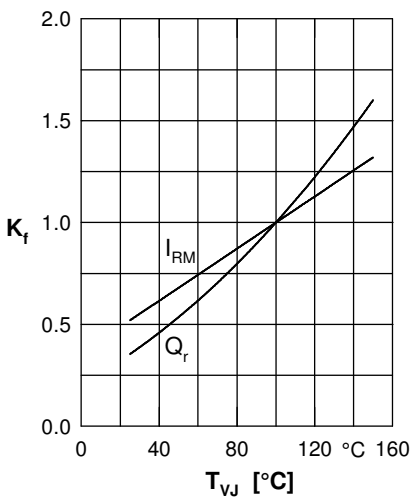


Fig. 4 Dynamic parameters Q_r , I_{RM} vs. junction temperature T_{VJ}

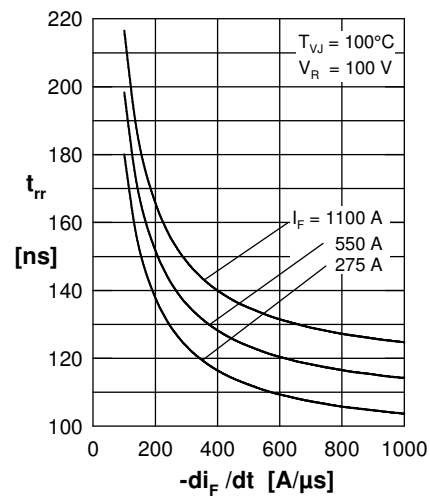


Fig. 5 Recovery time t_{rr} vs. $-di_F/dt$

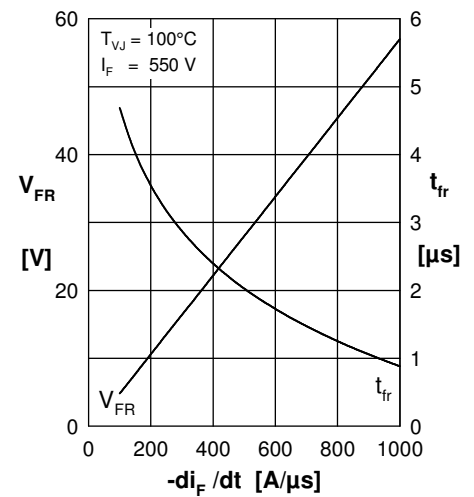


Fig. 6 Peak forward voltage V_{FR} & t_{fr} versus $-di_F/dt$

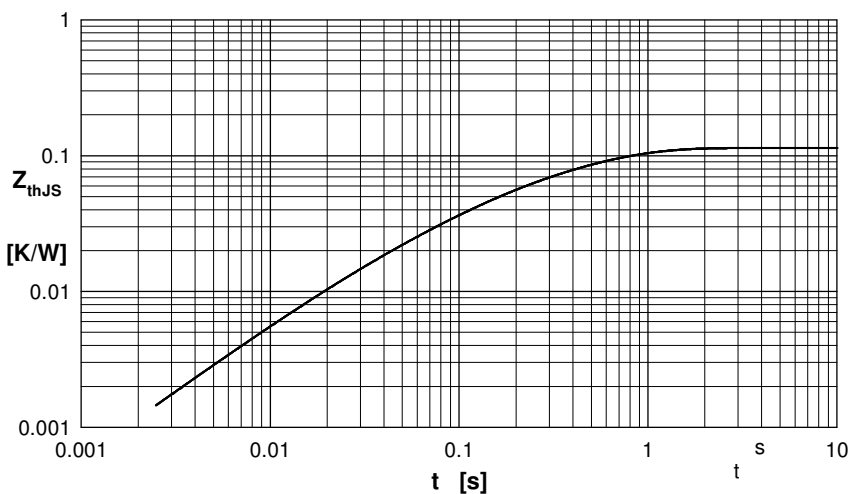


Fig. 7 Transient thermal impedance junction to heatsink

Constants for Z_{thJS} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.001	0.080
2	0.004	0.024
3	0.027	0.112
4	0.082	0.464